

Silicon NPN Power Transistors

2N6322

DESCRIPTION

- With TO-3 package
- High current and high power capability
- Low collector saturation voltage

APPLICATIONS

- For use in high current ,high power applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

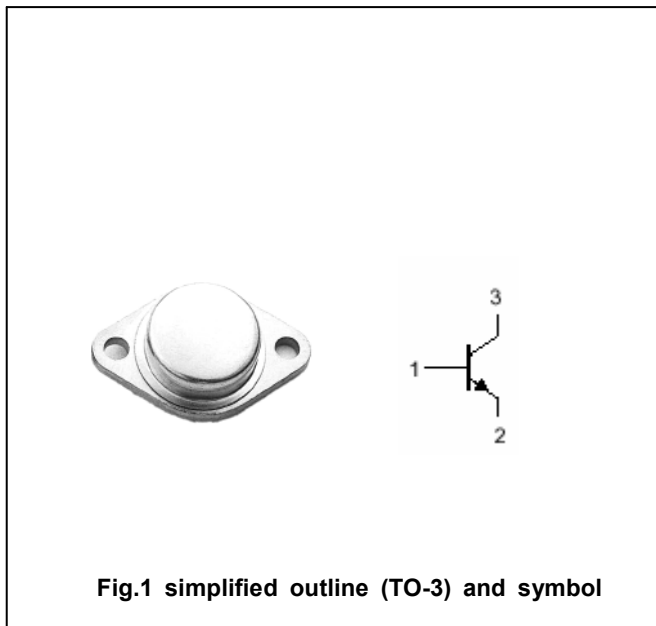


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		30	A
I _B	Base current		10	A
P _D	Total Power Dissipation	T _C =25□	200	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	0.5	□/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =2m A ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =2m A ; I _C =0	5			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =20A ; I _B =2A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =30A ; I _B =6A			3.0	V
V _{BE}	Base-emitter on voltage	I _C =30A ; V _{CE} =5V			2.5	V
I _{CEO}	Collector cut-off current	V _{CE} =100V ; I _B =0			2.0	mA
I _{CES}	Collector cut-off current	V _{CE} =300V ; V _{BE} =0			20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			20	μA
h _{FE-1}	DC current gain	I _C =5A ; V _{CE} =5V	40		150	
h _{FE-2}	DC current gain	I _C =20A ; V _{CE} =5V	12			
h _{FE-3}	DC current gain	I _C =30A ; V _{CE} =5V	6			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V	10			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)